

IN THE CLAIMS

This listing of claims replaces all prior listings.

1. (Previously Presented) A metal-oxide-compound semiconductor field effect transistor comprising:

- a nitride compound semiconductor wafer structure having an upper surface;
- a gate insulator structure comprising a first and second layer;
- said first layer substantially comprising compounds of gallium and oxygen
- said second layer comprising compounds of gallium and oxygen and at least one rare earth element;
- a gate electrode positioned on said gate insulator structure,
- source and drain regions self-aligned to said gate electrode; and
- source and drain ohmic contacts positioned on said source and drain areas;
- wherein gate electrode comprises a metal selected from the group refractory gate metals and combinations thereof;
- wherein the complete nitride MOS structure is built upon a a sapphire, silicon, SOI, AlN, or GaN substrate.

2.-70. Canceled.